

ABSTRACT

Using an attenuated phase shifting mask (Att.PSM) with square-section etch window there is the advantage of permitting good resolution and simultaneously increasing the depth of focus and the exposure latitude (the range of energy), improving
5 the lithographic process itself compared to the traditional masks, called binary. The Att.PSM masks introduce the problem of the side lobe effects which is solved with the present invention adopting a polygonal etch window with at least six sides, preferably with an octagonal shape.